



PRODUCT DATA SHEET



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Datasheet

Samples

Please note: Please check the JINGAO Semiconductor website to verify the updated device numbers. The most current and up-to-date ordering information can be found at www.jg-semi.cn. Please email any questions regarding the system integration to JINGAO_questions@jgsemi.com.



ESD Protection Diode

»Features

- 225Watts peak pulse power (tp = 8/20µs)
- Unidirectional configurations
- Solid-state silicon-avalanche technology
- Low clamping voltage
- Low leakage current
- IEC 61000-4-2 ±30kV contact ±30kV air
- IEC 61000-4-4 (EFT) 40A (5/50ns)
- IEC 61000-4-5 (Lightning) 5A (8/20µs)



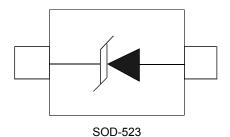
»Applications

- Microprocessor based equipment
- Personal Digital Assistants (PDA's)
- Notebooks, Desktops, and Servers
- Portable Instrumentation
- Pagers Peripherals

»Mechanical Data

- SOD523 package
- Molding compound flammability rating: UL 94V-0
- Packaging: Tape and Reel
- RoHS/WEEE Compliant

»Schematic & PIN Configuration





»Absolute Maximum Rating

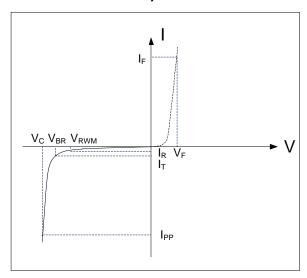
| Rating | Symbol | Value | Units | |
|--|------------------|----------------|--------------|--|
| Peak Pulse Power (t _p =8/20µs) | P _{PP} | 225 | Watts | |
| Peak Pulse Current (t _p =8/20µs) (note1) | I _{pp} | 5 | А | |
| ESD per IEC 61000-4-2 (Air) ESD per IEC 61000-4-2 (Contact) | V _{ESD} | 30 30 | kV | |
| Lead Soldering Temperature | T _L | 260(10seconds) | $^{\circ}$ C | |
| Junction Temperature | TJ | -55 to + 150 | $^{\circ}$ C | |
| Storage Temperature | T _{stg} | -55 to + 125 | $^{\circ}$ C | |

»Electrical Characteristics

| Parameter | Symbol | Conditions | Min | Typical | Max | Units |
|---------------------------|------------------|--|------|---------|------|-------|
| Reverse Stand-Off Voltage | V _{RWM} | | | | 24.0 | V |
| Reverse Breakdown Voltage | V_{BR} | I _T =1mA | 26.7 | | | V |
| Reverse Leakage Current | I _R | V _{RWM} =24.0V,T=25℃ | | | 0.5 | uA |
| Clamping Voltage | V _C | I _{PP} =5A,t _p =8/20μs | | 45 | | V |
| Junction Capacitance | C _j | V _R = 0V, f = 1MHz | | 30 | | pF |

»Electrical Parameters (TA = 25°C unless otherwise noted)

| Symbol | Parameter |
|--------|--|
| Ірр | Maximum Reverse Peak Pulse Current |
| Vc | Clamping Voltage @ IPP |
| Vrwm | Working Peak Reverse Voltage |
| Ir | Maximum Reverse Leakage Current @ Vrwм |
| VBR | Breakdown Voltage @ IT |
| Iτ | Test Current |
| | |
| | |



Note: $8/20\mu s$ pulsewaveform.



»Typical Characteristics

Figure 1: Peak Pulse Power vs. Pulse Time

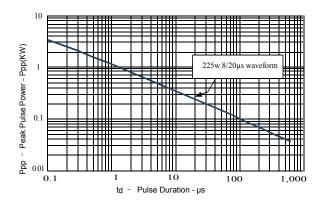


Figure 2: Power Derating Curve

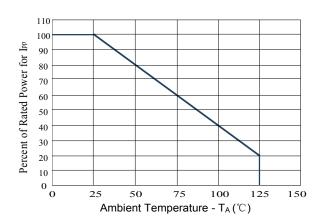


Figure3: Pulse Waveform

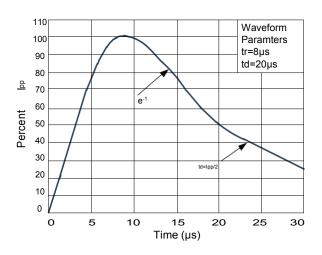
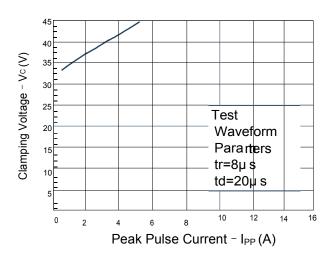
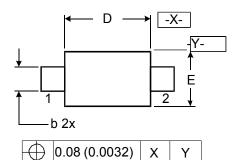


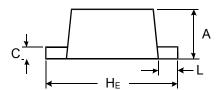
Figure 4: Clamping Voltage vs.lpp





»Outline Drawing – SOD523





DIMENSIONS

| SYMBOL | MILLIMETER | | INCHES | | |
|----------------|------------|------|--------|--------|--|
| | MIN | MAX | MIN | MAX | |
| Α | 0.50 | 0.70 | 0.020 | 0.028 | |
| b | 0.25 | 0.35 | 0.010 | 0.014 | |
| С | 0.07 | 0.20 | 0.0028 | 0.0079 | |
| D | 1.10 | 1.30 | 0.043 | 0.051 | |
| Е | 0.70 | 0.90 | 0.028 | 0.035 | |
| H _E | 1.50 | 1.70 | 0.059 | 0.067 | |
| L | 0.15 | 0.25 | 0.006 | 0.010 | |



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